EAST - [resistor.wsp.1]

File View Edit Tools Window Help

- Drafts
- Pending
- Active
  - L1: (285725) ROM or (read adj2 memory)
  - L2: (1865) 1 and ((PN adj junction) or ((p adj doped) and (n adj doped)))
  - L3: (1205) 2 and (trench$2 or opening$2 or hole$1)
  - L4: (47) 3 and (anneal$3 with ((single adj crystal) or crystal$5))
- Failed
  - (("5736461") or ("5970370") or ("6121139") or ("6136705") or ("6103610")).PN.

3 and (anneal$3 with ((single adj crystal) or crystal$5))

	U	T	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C				
16	P				US 20020105080	20020808	40	Method of forming an electronic device	257/749	257/E29.15 1;		Speakman; Stuart						
17	P				US 20020028541	20020307	151	Dense arrays and charge storage devices, and me	438/149	257/E27.02 6; 257/E29		Lee, Thomas H. et al.						
18	P				US 20020027793	20020307	41	Vertically stacked field programmable nonv	365/103	257/E27.07 3		Johnson; Mark G. et al.						
19	P				US 20020018355	20020214	41	Vertically stacked field programmable nonv	365/103	257/E27.07 3		Johnson; Mark G. et al.						
20					US 6780711 B2	20040824	40	Vertically stacked field programmable nonv	438/257	257/390; 257/391;		Johnson; Mark G. et al.	☑					
21					US 6735163 B2	20040511	29	Ultra-high density storage device with res	369/126	250/306; 369/101		Marshall; Daniel R.	P					
22					US 6713389 B2	20040330	37	Method of forming an electronic device	438/674	257/E29.15 1;		Speakman; Stuart	P					
23					US 6689644 B2	20040210	25	Vertically-stacked, field-programmable non	438/131	438/600		Johnson; Mark G.	P					
24					US 6642112 B1	20031104	17	Non-oxidizing spacer densification method fo	438/275	257/E21.63 7;		Lowe; Brett D. et al.	P					
25					US 6525953 B1	20030225	26	Vertically-stacked, field-programmable, non	365/63	365/225.7; 365/51;		Johnson; Mark G.	P					
26					US 6503831 B2	20030107	36	Method of forming an electronic device	438/674	257/E29.15 1;		Speakman; Stuart	P					
27					US 6483736 B2	20021119	41	Vertically stacked field programmable nonv	365/130	257/E27.07 3;		Johnson; Mark G. et al.	P					
28					US 6404647 B1	20020611	14	Solid-state mass memory storage device	361/760	361/684; 361/685;		Minne'; Mark W.	P					
29					US 6351406 B1	20020226	42	Vertically stacked field programmable nonv	365/103	365/164		Johnson; Mark G. et al.	P					
30					US 6198137 B1	20010306	19	Semiconductor device	257/365	257/347; 257/E21.70		Ashida; Tsutomu	P					
31					US 6185122 B1	20010206	40	Vertically stacked field programmable nonv	365/103	257/E27.07 3;		Johnson; Mark G. et al.	P					
32					US 6093243 A	20000725	154	Semiconductor device and its fabricating met	117/8	117/9; 257/E21.01		Okada; Takako et al.	P					
33					US 6066872 A	20000523	153	Semiconductor device and its fabricating met	257/309	257/534; 257/E21.01		Okada; Takako et al.	P					
34					US 6034882 A	20000307	38	Vertically stacked field programmable nonv	365/103	257/E27.07 3;		Johnson; Mark G. et al.	P					
35					US 5879447 A	19990309	152	Semiconductor device and its fabricating met	117/8	117/9; 117/930;		Okada; Takako et al.	P					

EAST - [resistur wsp.1]

File Ver Edit Tools Window Help

- Drafts
- Pending
- Active
  - L1: (22191) anneal$3.clm. or RTA.clm.
  - L2: (2834) 1 and (single adj crystal)
  - L3: (1100) 2 and (opening$1 or trench$2)
  - L4: (111) 3 and (ROM or (OTP adj ROM) or (read adj2 memory) or
  - L5: (90) 4 and insulat$3
  - L6: (75) 5 and (dop$3 or (p adj doped) or (n adj doped))
  - L7: (2) 6 and (one adj time adj programmable)
  - L8: (36) 6 and (opening$1.clm. or trench$2.clm. or hole$1.clm.
  - L9: (1618) (OTP adj ROM) or (one adj time adj programmable)
  - L10: (347) 9 and ((single adj crystal) or crystal$5)
  - L11: (53) 10 and anneal$3
  - L12: (41) 11 and (junction or (pn adj junction) or (p adj dope
  - L14: (2) 13 and anneal$3.clm.
  - L15: (36) 12 and (trench$2 or opening$1 or hole$1)
- Failed
  - (("5736461") or ("5970370") or ("6121139") or ("6136705") or (
- Saved
- Favorites
- Tagged (8)

12 and (trench$2 or opening$1 or hole$1)

Default Operator: OR

U	A	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C				
1				US 20040235246	20041125	11	Fabrication of an OTP-EPROM having reduce	438/257			Wu, Xiaoju et al.						
2				US 20040214389	20041028	36	Semiconductor latches and SRAM devices	438/202			Madurawe, Raminda Udava						
3				US 20040161893	20040819	22	Methods for enhancing capacitors having rough	438/240	257/E21.013		Thakur, Randhir P.S. et al.						
4				US 20040155302	20040812	44	Three-dimensional memory cells and periph	257/390	257/E27.026		Zhang, Guobiao						
5				US 20040155301	20040812	44	Three-dimensional-memory-based self-test integ	257/390	257/E27.026		Zhang, Guobiao						
6				US 20040072397	20040415	16	Non-oxidizing spacer densification method fo	438/200	257/E21.637		Lowe, Brett D. et al.						
7				US 20040016976	20040129	44	Peripheral circuits of electrically programmab	257/390	257/E27.026		Zhang, Guobiao						
8				US 20040012053	20040122	46	Electrically programmable three-dime	257/390	257/E27.026		Zhang, Guobiao						
9				US 20040007746	20040115	44	Electrically programmable three-dime	257/390	257/E27.026		Zhang, Guobiao						
10				US 20030206429	20031106	39	VERTICALLY STACKED FIELD PROGRAMMABLE NONV	365/103	257/E27.073		Subramanian, Vivek et al.						
11				US 20030203577	20031030	18	NON-OXIDIZING SPACER DENSIFICATION METHOD FO	438/275	257/E21.637		Lowe, Brett D. et al.						
12				US	20030703	31	Vertically-stacked	438/257			Johnson, Mark G.						